

FIG.1
RELATED ART

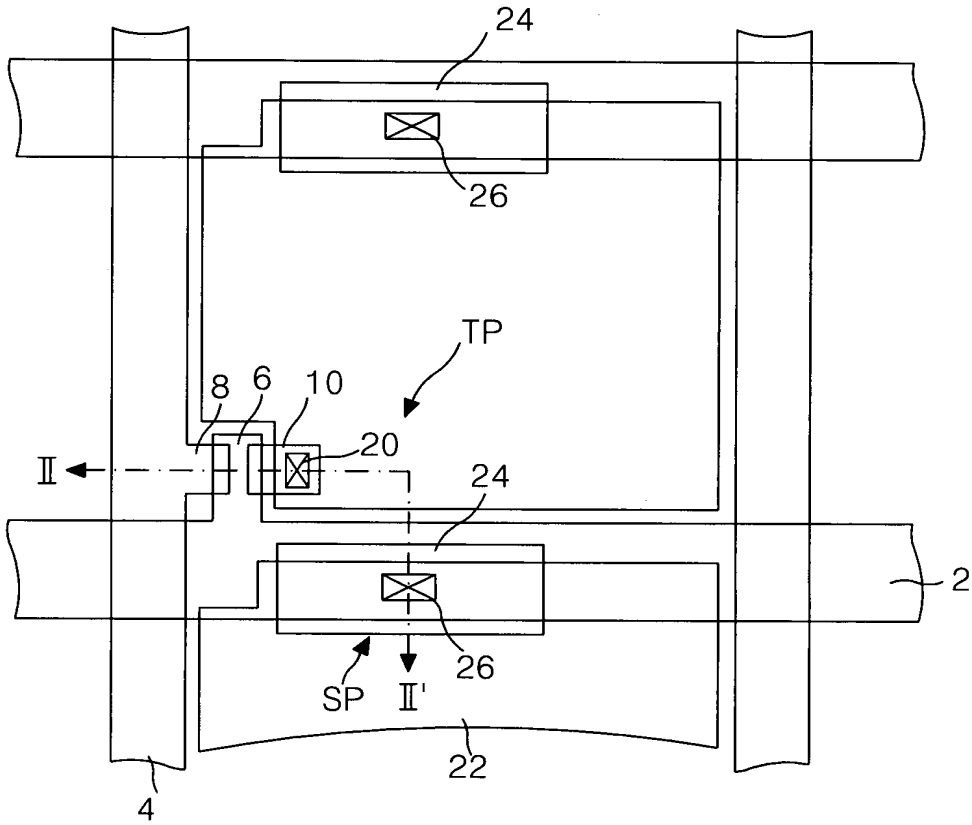


FIG. 2
RELATED ART

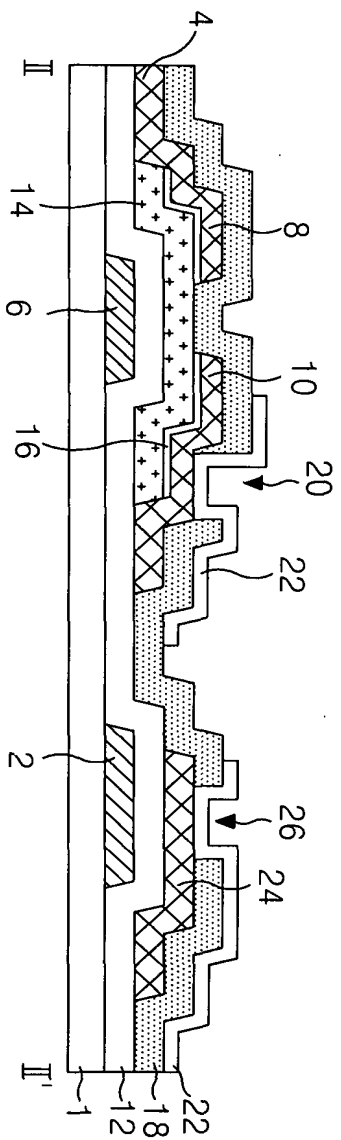


FIG. 3A
RELATED ART

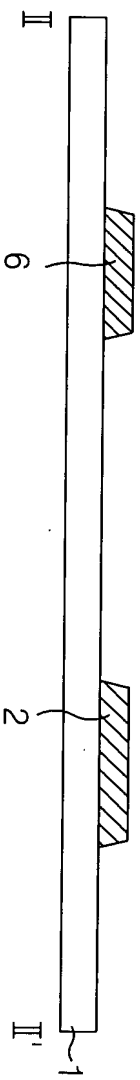
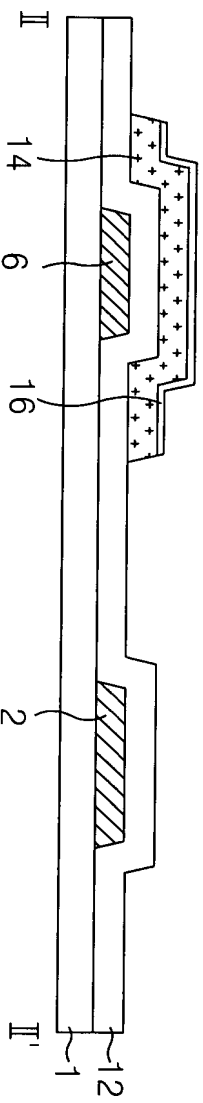
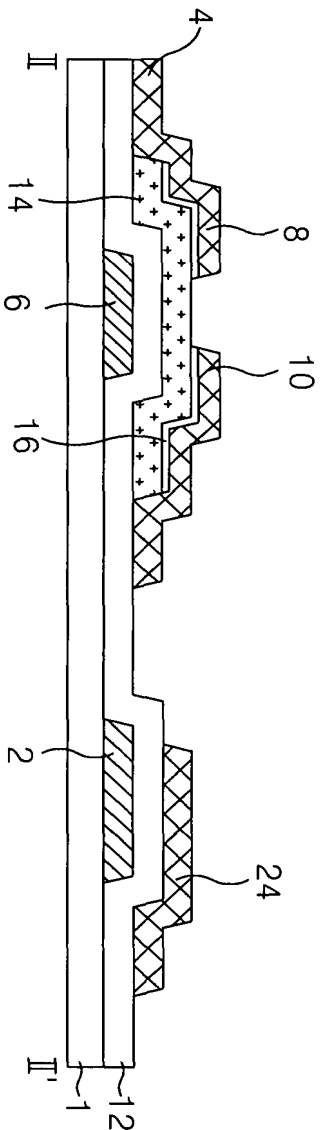


FIG. 3B
RELATED ART





This cross-sectional view shows a semiconductor device with a multi-layered structure. At the top, a layer with a cross-hatch pattern (4) is shown. Below it is a layer with a dotted pattern (8). A central layer with a '+' pattern (10) is sandwiched between two layers with a cross-hatch pattern (14 and 16). The bottom of the device features a series of layers: a cross-hatch patterned layer (2), a dotted patterned layer (24), and a cross-hatch patterned layer (26). The entire structure is supported by a substrate (1) with a cross-hatch pattern. The device is divided into two main sections, II and II', by a vertical line. A dashed line (6) is shown within the central layer (10). A dashed line (12) is shown within the bottom layer (2). A dashed line (18) is shown within the bottom layer (26). A dashed line (20) is shown within the bottom layer (24). A dashed line (22) is shown within the bottom layer (26).

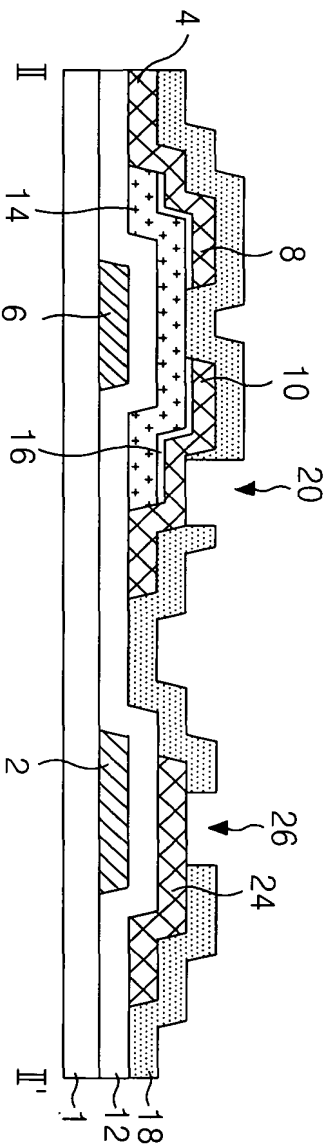


FIG. 3E
RELATED ART

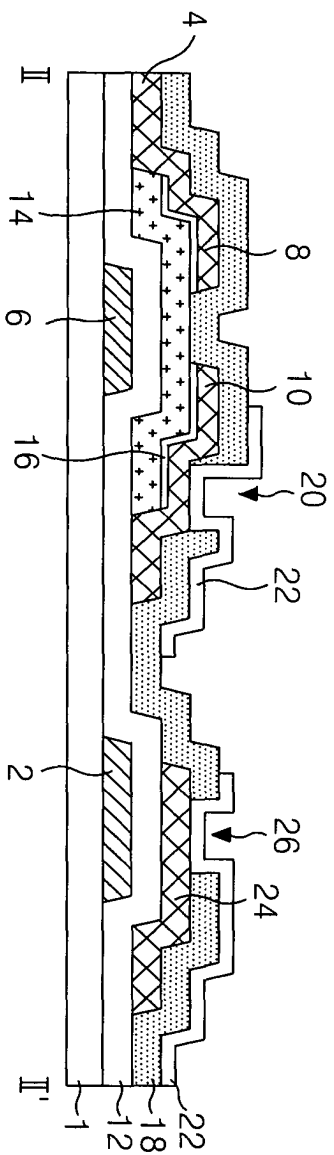


FIG. 4A
RELATED ART

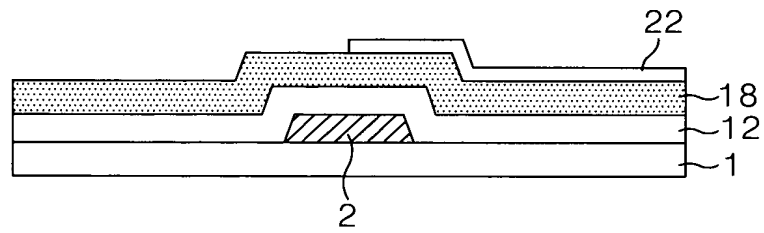


FIG. 4B
RELATED ART

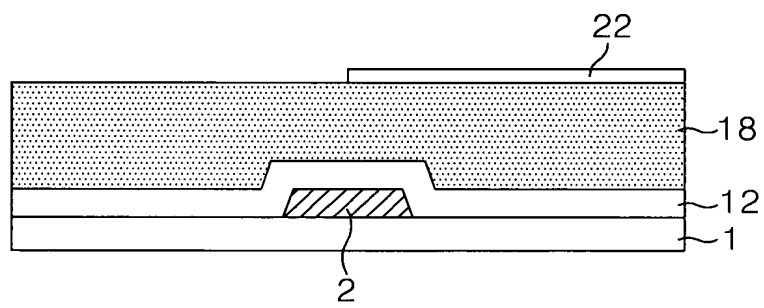


FIG. 5

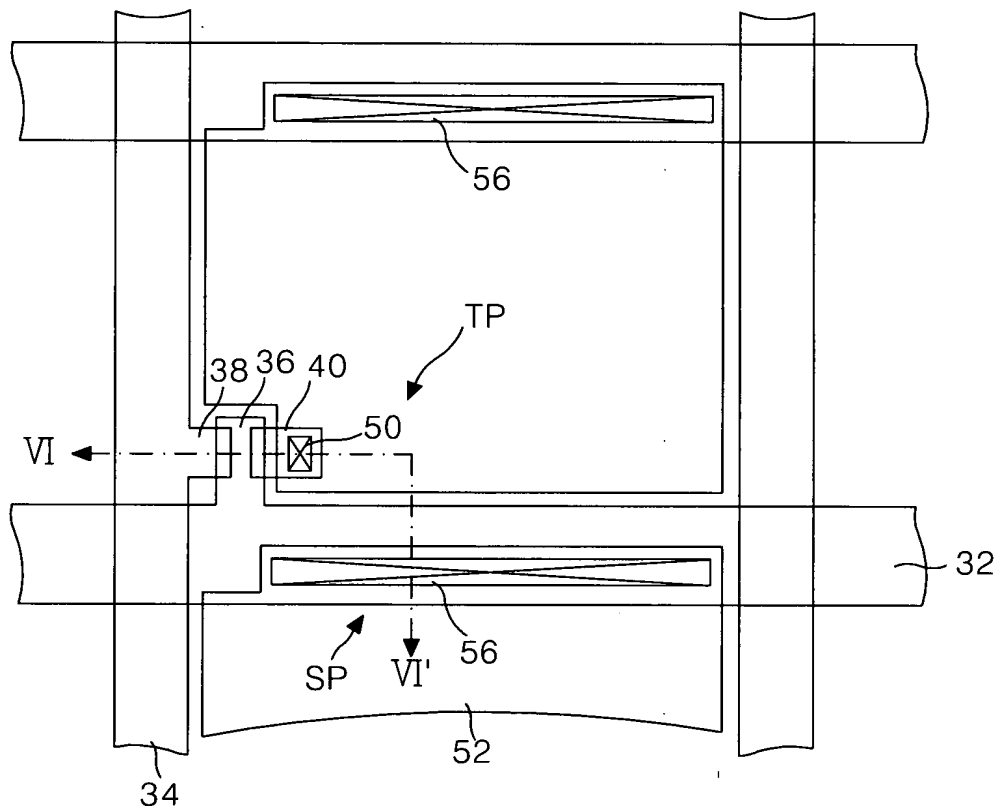


FIG. 6

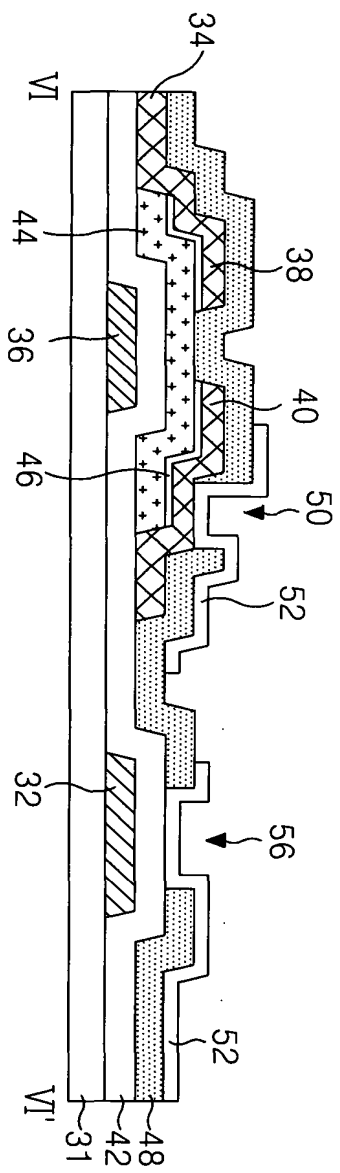


FIG. 7A

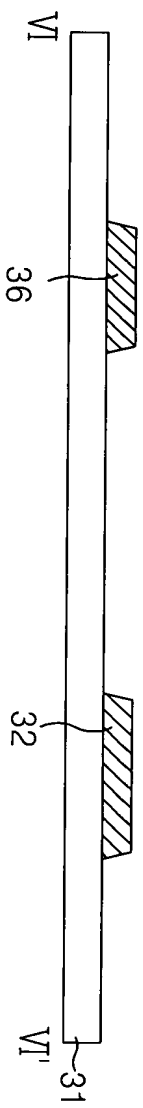


FIG. 7B

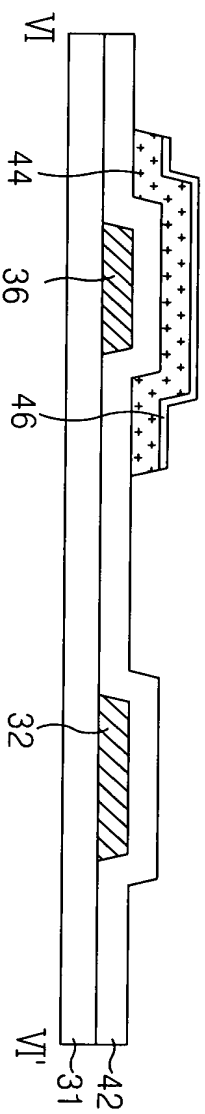


FIG. 7C

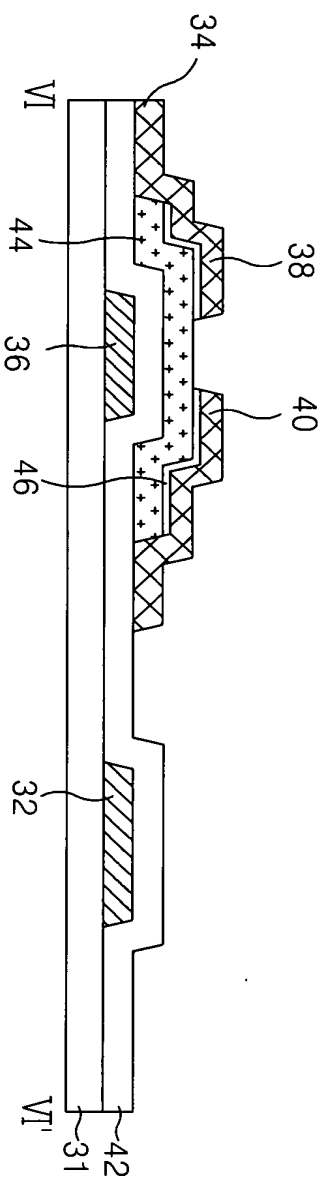


FIG. 7D

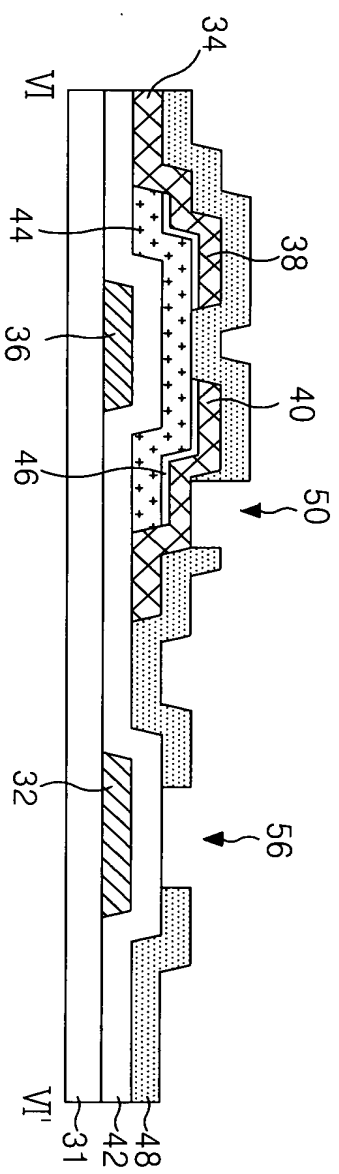


FIG. 7E

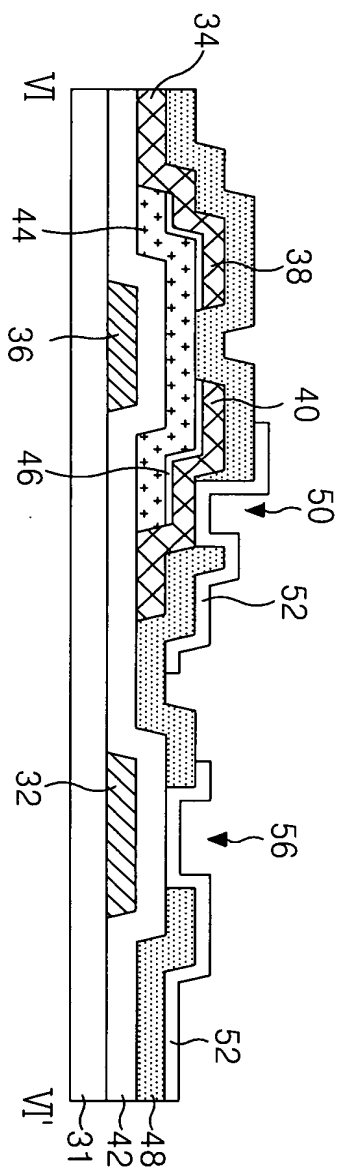


FIG. 8A

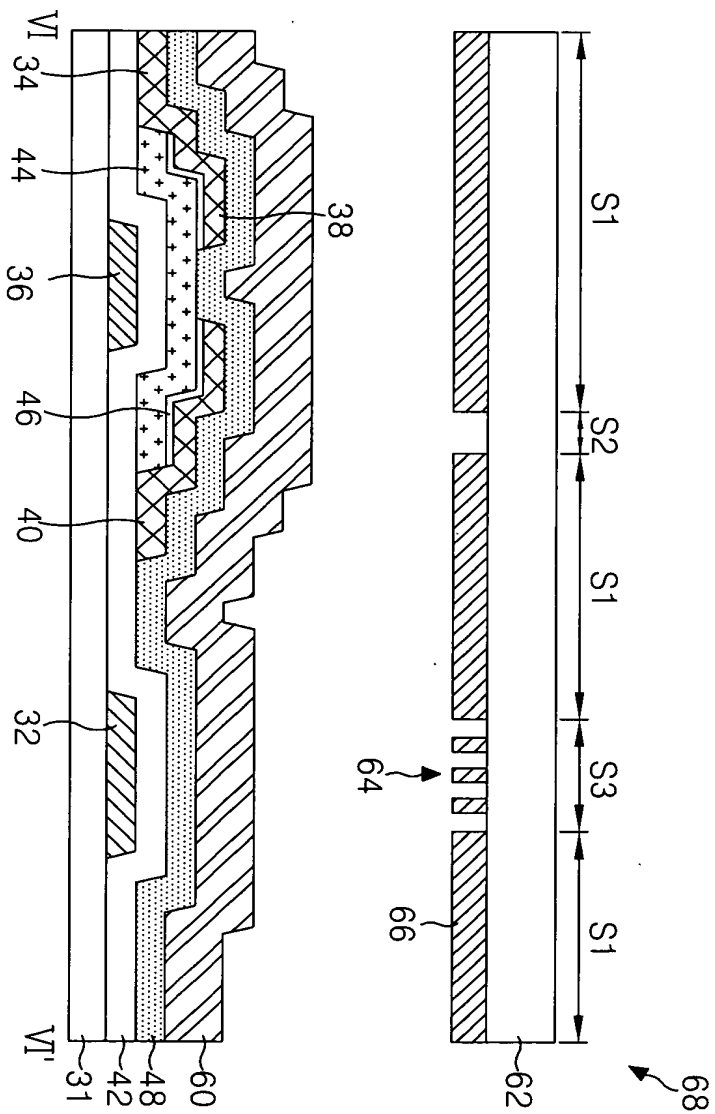


FIG. 8B

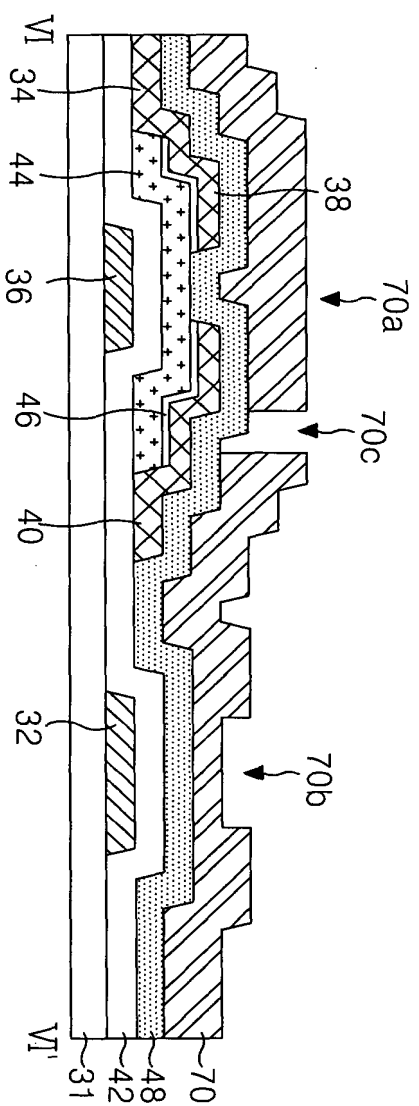


FIG. 8C

